**Thyristor Module** 

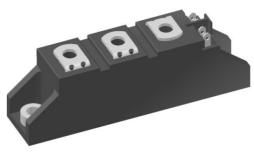
## **MCMA50P1600TA**

$V_{\text{RRM}}$	<i>=</i> 2x 1600 V			
I <sub>tav</sub>	=	50 A		
Vτ	=	1.17 V		

Phase leg

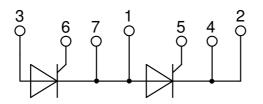
Part number

**MCMA50P1600TA** 



Backside: isolated **E**72873

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### Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

### **Applications:**

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

### Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

### Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office. Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747and per semiconductor unless otherwise specified

# LIXYS

# **MCMA50P1600TA**

Thyristo				1	Ratings		
Symbol	Definition	Conditions		min.	typ.	max.	Uni
V <sub>RSM/DSM</sub>	max. non-repetitive reverse/forwa	0 0	$T_{VJ} = 25^{\circ}C$			1700	\
V <sub>RRM/DRM</sub>	max. repetitive reverse/forward bl		$T_{VJ} = 25^{\circ}C$			1600	\
R/D	reverse current, drain current	$V_{R/D} = 1600 V$	$T_{VJ} = 25^{\circ}C$			100	μ/
		V <sub>R/D</sub> = 1600 V	$T_{VJ} = 140^{\circ}C$			6	m/
V <sub>T</sub>	forward voltage drop	$I_{T} = 50 A$	$T_{VJ} = 25^{\circ}C$			1.25	١
		$I_{T} = 100 \text{ A}$				1.48	١
		$I_{T} = 50 \text{ A}$	$T_{VJ} = 125 ^{\circ}C$			1.17	١
		$I_{T} = 100 \text{ A}$				1.44	١
ITAV	average forward current	$T_c = 85^{\circ}C$	T <sub>vJ</sub> = 140°C			50	ŀ
I T(RMS)	RMS forward current	180° sine				79	ļ
V <sub>T0</sub>	threshold voltage		T <sub>vJ</sub> = 140°C			0.89	١
r <sub>T</sub>	slope resistance } for power lo	oss calculation only				5.3	m۵
<b>R</b> <sub>thJC</sub>	thermal resistance junction to cas	e				0.7	K/W
R <sub>thCH</sub>	thermal resistance case to heatsi				0.20		K/W
P <sub>tot</sub>	total power dissipation		$T_c = 25^{\circ}C$		00	160	W
I <sub>TSM</sub>	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{v,i} = 45^{\circ}C$			800	1
• ISM		t = 8,3  ms; (60  Hz),  sine	$V_{\rm R} = 0 V$			865	ļ
		t = 0,0  ms; (50  Hz),  sine t = 10  ms; (50  Hz),  sine	$T_{V,I} = 140^{\circ}C$			680	ļ
		t = 8,3  ms; (60  Hz),  sine	$V_{\rm NJ} = 0$ V			735	, ,
l²t	value for fusing		$T_{VJ} = 45^{\circ}C$				1
1-(	value for fusing	t = 10 ms; (50 Hz), sine				3.20	kA <sup>2</sup>
		t = 8,3 ms; (60 Hz), sine	$V_{\rm R} = 0 V$			3.12	
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 140 ^{\circ}\text{C}$			2.31	kA <sup>2</sup> s
_		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			2.25	
CJ	junction capacitance	$V_{R} = 400 V$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		32		pF
P <sub>GM</sub>	max. gate power dissipation	t <sub>P</sub> = 30 μs	$T_c = 140 ^{\circ}C$			10	N
		t <sub>P</sub> = 300 μs				5	N
P <sub>GAV</sub>	average gate power dissipation					0.5	N
(di/dt) <sub>cr</sub>	critical rate of rise of current	$T_{vJ} = 140 ^{\circ}C; f = 50  Hz$ re	petitive, $I_T = 150 A$			150	A/μ
		$t_{P}$ = 200 µs; di <sub>G</sub> /dt = 0.45 A/µs;					   
		$I_{G} = 0.45 \text{ A}; \text{ V } = \frac{2}{3} \text{ V}_{DRM}$ no	on-repet., $I_{T} = 50 \text{ A}$			500	A/μ
(dv/dt) <sub>cr</sub>	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{vJ} = 140^{\circ}C$			1000	V/μ
		R <sub>GK</sub> = ∞; method 1 (linear voltag	ge rise)				
V <sub>gt</sub>	gate trigger voltage	$V_{D} = 6 V$	$T_{VJ} = 25^{\circ}C$			1.5	١
			$T_{vJ} = -40 ^{\circ}\text{C}$			1.6	١
I <sub>GT</sub>	gate trigger current	$V_{D} = 6 V$	$T_{VJ} = 25^{\circ}C$			78	m/
ai	0 00		$T_{VJ} = -40^{\circ}C$			200	m/
V <sub>gd</sub>	gate non-trigger voltage	$V_{\rm D} = \frac{2}{3} V_{\rm DBM}$	$T_{VJ} = 140^{\circ}C$			0.2	١
I <sub>GD</sub>	gate non-trigger current	D , C DRM	. vj			5	m/
	latching current	t <sub>p</sub> = 10 μs	$T_{VJ} = 25^{\circ}C$			200	m/
I.		· ·				200	111/
	halding average	$I_{\rm G} = 0.45 \text{A};  \text{di}_{\rm G}/\text{dt} = 0.45 \text{A}/\mu\text{s}$				100	
I <sub>H</sub>	holding current	$V_{\rm D} = 6 V R_{\rm GK} = \infty$	$T_{VJ} = 25 ^{\circ}C$			100	mA
t <sub>gd</sub>	gate controlled delay time	$V_{\rm D} = 1/2 V_{\rm DRM}$	$T_{vJ} = 25 \degree C$			2	μ
		$I_{\rm G} = 0.45 \text{A};  \text{di}_{\rm G}/\text{dt} = 0.45 \text{A}/\mu\text{s}$					
t <sub>q</sub>	turn-off time	$V_{R} = 100 \text{ V}; I_{T} = 50 \text{ A}; \text{ V} = \frac{2}{3}$			150		μ
		$di/dt = 10 \text{ A}/\mu \text{s} dv/dt = 20 \text{ V}/\mu \text{s}$	μs t <sub>p</sub> = 200 μs				1

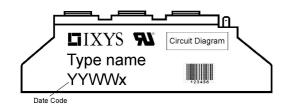
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# XYS

# **MCMA50P1600TA**

Package TO-240AA			Ratings					
Symbol	Definition	Conditions			min.	typ.	max.	Unit
	RMS current	per terminal					100	Α
T <sub>vj</sub>	virtual junction temperature				-40		140	°C
T <sub>op</sub>	operation temperature				-40		125	°C
T <sub>stg</sub>	storage temperature				-40		125	°C
Weight						81		g
M <sub>D</sub>	mounting torque				2.5		4	Nm
M <sub>T</sub>	terminal torque				2.5		4	Nm
d <sub>Spp/App</sub>	creepage distance on surface   striking distance thr		terminal to terminal	13.0	9.7			mm
<b>d</b> <sub>Spb/Apb</sub>	creepage distance on suna		terminal to backside	16.0	16.0			mm
V	isolation voltage t = 1 sec	t = 1 second		4800				V
	t = 1 minute		50/60 Hz, RMS; lıso∟ ≤ 1 mA		4000			V



### Part description

M = Module

M = Module C = Thyristor (SCR) M = Thyristor A = (up to 1800V) 50 = Current Rating [A] P = Phase leg 1600 = Reverse Voltage [V]

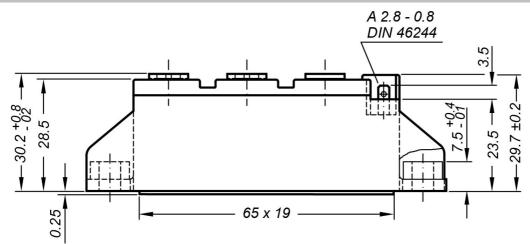
TA = TO-240AA-1B

ſ	Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.	
	Standard	MCMA50P1600TA	MCMA50P1600TA	Box	36	513950	

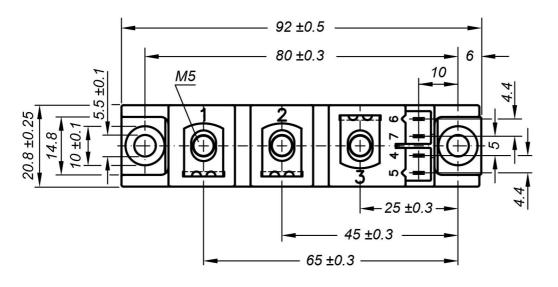
Equiva	alent Circuits for	Simulation	* on die level	T <sub>vJ</sub> = 140 °C
	)[	Thyristor		
V <sub>0 max</sub>	threshold voltage	0.89		V
$\mathbf{R}_{0 \text{ max}}$	slope resistance *	4.1		mΩ

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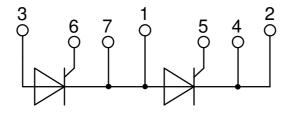
## Outlines TO-240AA



General tolerance: DIN ISO 2768 class "c"



Optional accessories: Keyed gate/cathode twin plugs Wire length: 350 mm, gate = white, cathode = red UL 758, style 3751 Type **ZY 200L** (L = Left for pin pair 4/5) Type **ZY 200R** (R = Right for pin pair 6/7)

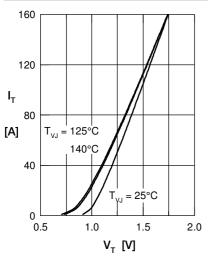


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## **MCMA50P1600TA**

40

### Thyristor



800

ITSM

[A]

400

100.0

10.0

1.0

0.1

0.01

t<sub>gd</sub>

٦

Fig. 1 Forward characteristics

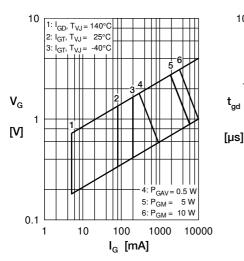


Fig. 4 Gate voltage & gate current

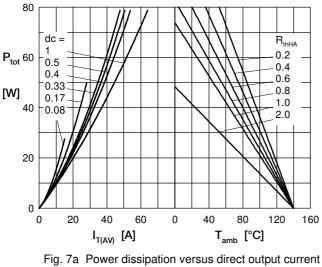


Fig. 7b and ambient temperature



10

0.20

0.10

0.00

1

10000

0.0100

0.0500

0.1500

0.3200

0.1700

1000

1 2

3

4

5

100

t [ms] Fig. 8 Transient thermal impedance junction to case

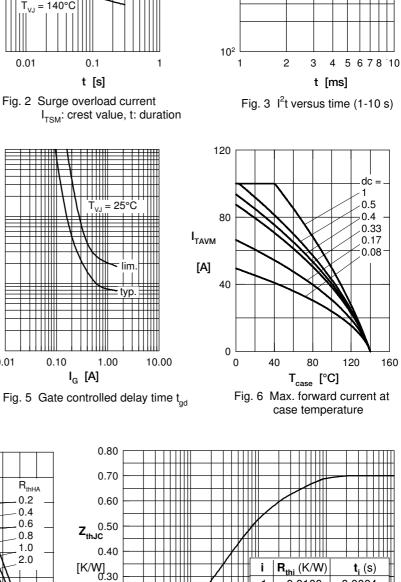
0.0004

0.0090

0.0140

0.0500

0.3600



104

l<sup>2</sup>t

[A<sup>2</sup>s]

50 Hz, 80% V

 $\mathsf{T}_{\mathsf{VJ}}$ = 45°C  $V_R = 0 V$ 

 $T_{VJ} = 45^{\circ}C$